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~~11.~~ (Amended) A method of fabricating a semiconductor device having a low dielectric interlayer insulation layer, comprising:

~~stacking a silicon oxycarbide layer (SiOC) as the low dielectric interlayer insulation layer on a substrate;~~

~~after the silicon oxycarbide layer is formed, treating the silicon oxycarbide layer with plasma; and~~

~~forming an interconnection at the silicon oxycarbide layer using a damascene process.~~